

DOCUMENT-IDENTIFIER: US 20030064323 A1

TITLE: Method for forming a pattern and method of  
manufacturing semiconductor device

----- KWIC -----

Detail Description Paragraph - DETX (129):

[0168] As for the light source for the exposure light, it may be g-ray (wavelength=436 nm) or i-ray (wavelength=365 nm) of a mercury lamp; an excimer laser such as XeF (wavelength=351 nm), XeCl (wavelength=308 nm), KrF (wavelength=248 nm), KrCl (wavelength=222 nm), ArF (wavelength=193 nm), F.sub.2 (wavelength=157 nm); X-ray; electron beam; ion beam; etc.